



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
001/	0.55Ω @ V <sub>GS</sub> = 4.5V	0.75A
20V	0.75Ω @ V <sub>GS</sub> = 2.5V	0.63A

#### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected up to 1.5kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- **Battery Charging**
- **Power Management Functions**
- DC-DC Converters
- Portable Power Adaptors

#### **Mechanical Data**

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: Collector Dot
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @4)
- Weight: 0.001 grams (Approximate)

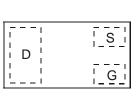




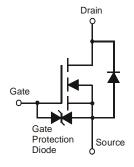


X1-DFN1006-3

**Bottom View** 



Top View Package Pin Configuration



**Equivalent Circuit** 

### Ordering Information (Note 4)

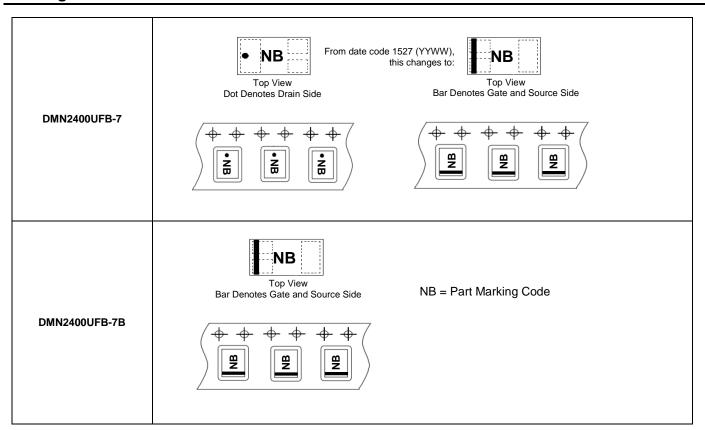
Part Number	Case	Packaging
DMN2400UFB-7	X1-DFN1006-3	3,000/Tape & Reel
DMN2400UFB-7B	X1-DFN1006-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



## **Marking Information**





## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			$V_{GSS}$	±12	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I <sub>D</sub>	0.75 0.55	А
Continuous Drain Current (Note 5) $V_{GS} = 2.5V$ Steady $T_A = +25^{\circ}C$ State $T_A = +85^{\circ}C$		I <sub>D</sub>	0.63 0.45	А	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	3	Α

## **Thermal Characteristics** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_{D}$	0.47	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	258	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

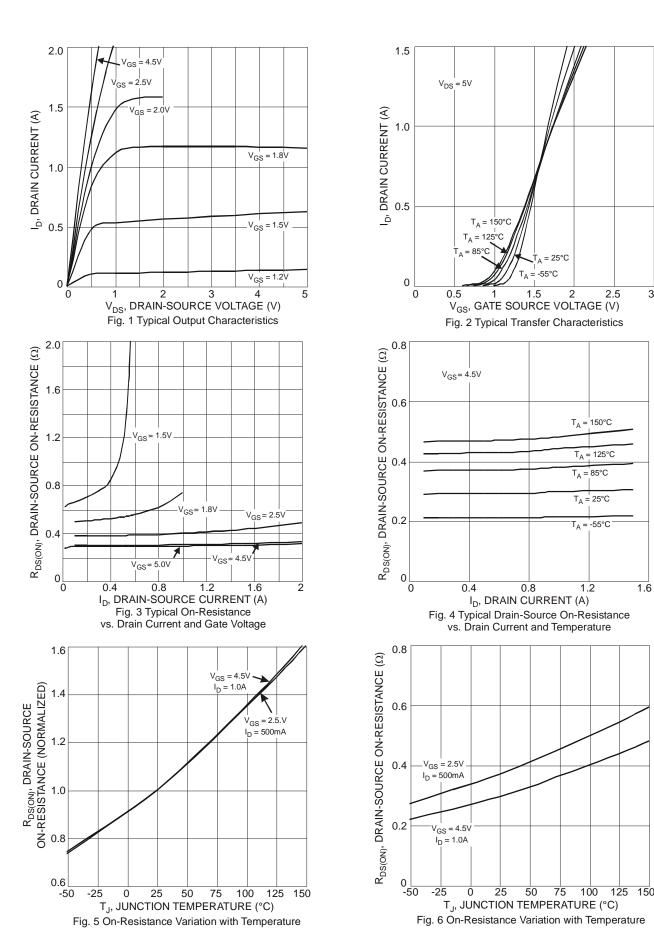
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V$ , $I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +2	25°C I <sub>DSS</sub>	-	-	100	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±1.0	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±50	μΑ	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	-	0.9	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
		-	-	0.55	Ω	$V_{GS} = 4.5V, I_D = 600mA$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	-	0.75		$V_{GS} = 2.5V, I_D = 500mA$	
		-	-	0.9		$V_{GS} = 1.8V, I_D = 350mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	1.0	-	S	$V_{DS} = 10V, I_D = 400mA$	
Diode Forward Voltage (Note 7)	V <sub>SD</sub>		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	36.0	-	pF	101/11/	
Output Capacitance	Coss	-	5.7	-	pF	$V_{DS} = 16V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	4.2	-	pF	71 = 1.010102	
Total Gate Charge	Qg	-	0.5	-	nC	V <sub>GS</sub> =4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA	
Gate-Source Charge	Q <sub>gs</sub>	-	0.07	-	nC		
Gate-Drain Charge	$Q_{gd}$	-	0.1	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	4.11	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_{L} = 47\Omega, R_{G} = 10\Omega,$ $I_{D} = 200\text{mA}$	
Turn-On Rise Time	t <sub>r</sub>	-	3.82	-	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	14.8	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	9.6	-	ns		

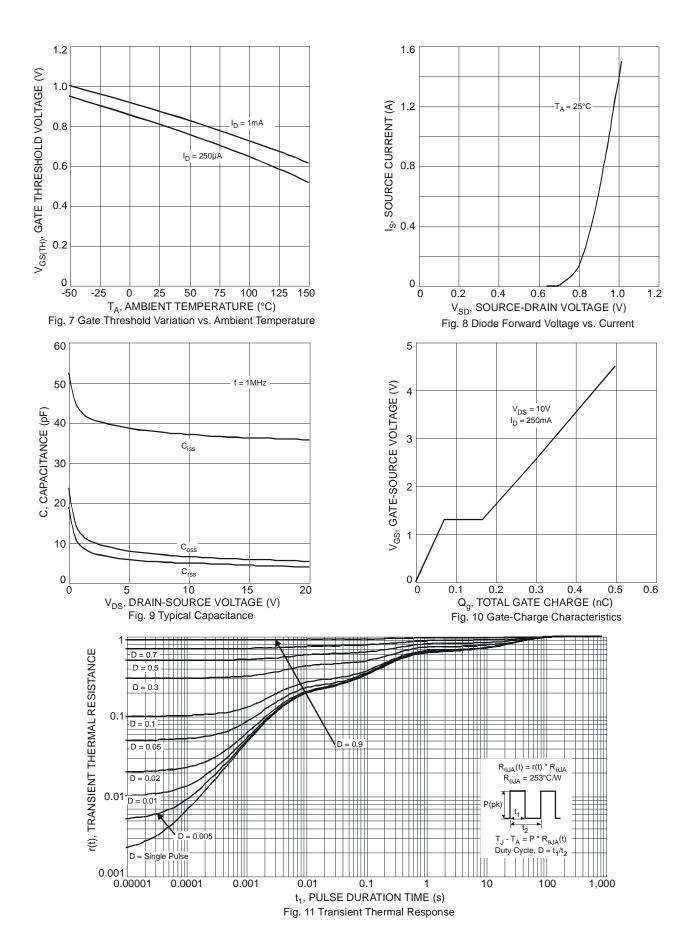
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 5. Device mounted on FK-4 PCB, with minimum recommended pad layout.
  6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

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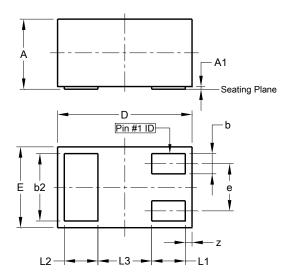






## **Package Outline Dimensions**

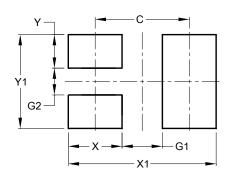
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
E	0.55	0.675	0.60		
е	ı	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Υ	0.25
Y1	0.70



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